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Supporting Information

Understanding the Impact of Annealing on Interface and Border Traps in the Cr/HfO₂/Al₂O₃/MoS₂ System

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Optical photos of a representative device

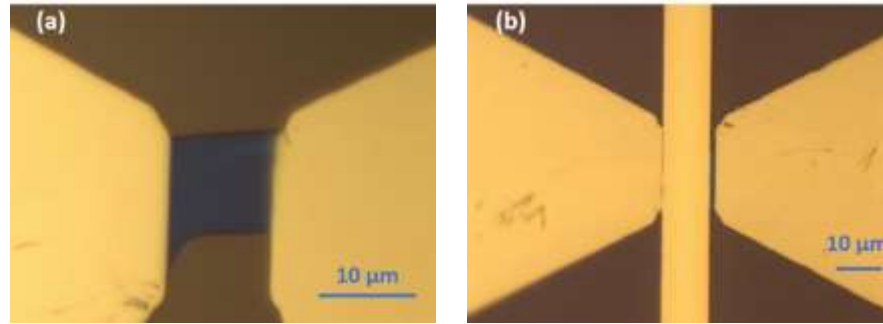


Fig. S1. Optical photos of a representative device (a) After S/D metal deposition; (b) After gate metal deposition.

Table S-I. Parameters used/extracted in simulation

	MoS ₂	Al ₂ O ₃	HfO ₂
Electron affinity (eV)	4.3	1.45	2.2
Band gap (eV)	1.25	8.8	6.0
Tunneling effective mass (m_0)	0.53	0.2	0.5
Doping or oxide charge (cm ⁻³)	6×10^{17} - 9×10^{18}	7.45×10^{19} - 1.35×10^{20}	1×10^{20}

Interface traps

Relaxation energy 0.72 eV

Capture cross section 8×10^{-20} - 1.6×10^{-18} cm²

Border traps

Relaxation energy 0.72 eV

Capture cross section 5×10^{-18} cm²

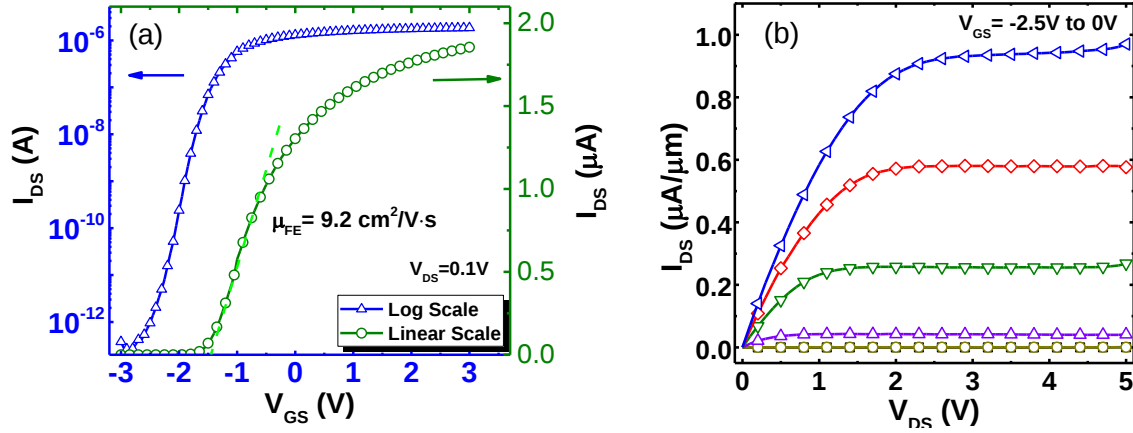


Fig. S2. Typical (a) I_{DS} - V_{GS} (b) I_{DS} - V_{DS} characteristics for the as-fabricated MoS₂ transistors in this work with peak field effect mobility μ_{FE} values around $9.2 \text{ cm}^2/\text{V}\cdot\text{s}$ and I_{ON}/I_{OFF} ratios larger than 10^6 . Since there is inherent variability in MoS₂ flakes, similar variability was observed in the current characteristics, such as subthreshold slope variation associated with the frequency dispersion dependence of the C-V data. (Data above is for Device 3.)

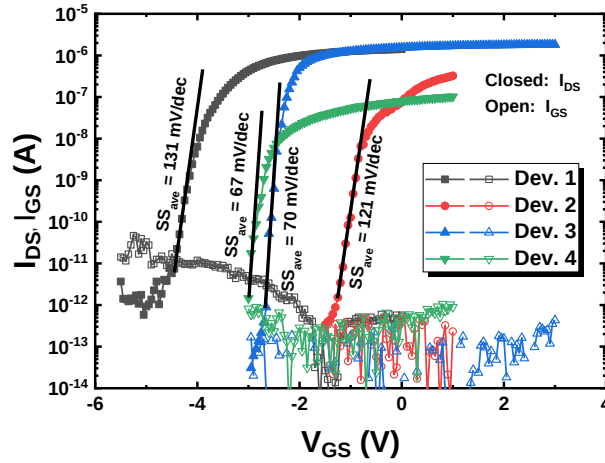


Fig. S3. Typical (a) I_{DS} - V_{GS} (closed symbols) and I_{GS} - V_{GS} (open symbols) characteristics for the as-fabricated MoS₂ transistors used in this work. The plots illustrate the extracted average subthreshold slope (SS) which correlate with the extracted D_{it} of Table I. Furthermore, extremely low gate leakage currents were obtained for these devices.

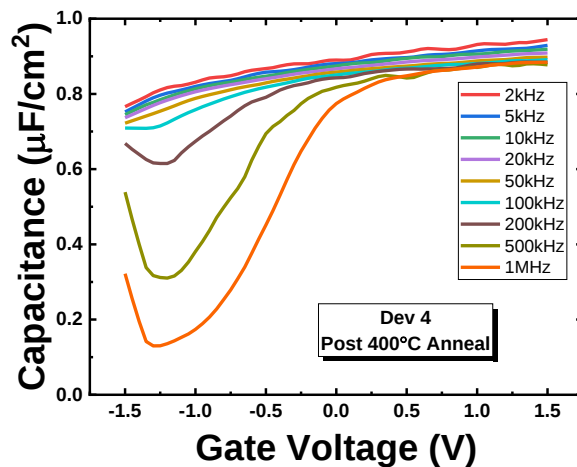


Fig. S4. Multi-frequency C-V result for device #4 after a 400°C FGA. The 400°C FGA largely degrades the interfaces and performance of devices with $\text{HfO}_2/\text{Al}_2\text{O}_3/\text{MoS}_2$ stacks where confirmation of this is observed in device #4, which originally showed no appreciable D_{it} (Fig. 4). The C-V data should have simply reproduced the pre-annealed results for device #4, if 400°C did not degrade the device.